

DOCUMENT CHANGE REQUEST

411 Originator: S Jeffery - ESCC DCR number Changes required for: General Date: 2008/06/18 Organisation: ESA/ESTEC Date sent: 2008/06/18 Status: IMPLEMENTED Title: Transistors Low Power NPN, based on type 2N2219A Number: 2 5201/003 Issue: Other documents affected: Page: Para. 2.4.1 Page 9 Paragraph: Para. 2.4.1 Page 9 Original wording: Proposed wording: See attachment Justification: Correction of editorial error which was introduced when the specification was converted to ESCC Format (Issue 2) Attachments: 5201003_Issue_3.pdf, null Modifications: N/A Approval signature: 12.6c f(an-+ Date signed: 2008-06-18



ISSUE 2

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	3001	I _C = 10μA, Bias Condition D	75	up.	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	3011	I _C = 10mA, Bias Condition D Note 1	40	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	3026	I _E = 10μA, Bias Condition D	6	-	V
Collector-Base Cut- off Current	l _{CBO}	3036	V _{CB} = 60V, Bias Condition D	-	10	nA
Emitter-Base Cut- off Current	I _{EBO}	3061	V _{EB} = 3V, Bias Condition D		10	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)1}	3071	I _C =150mA I _B =15mA Note 1	-	300	mV
	V _{CE(sat)2}	3071	I _C =500mA I _B =50mA Note 1	-	1	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	3066	Test Condition A I _C =150mA I _B =15mA Note 1	-	1.2	V
Forward-Current Transfer Ratio	h _{FE1}	3076	V _{CE} =10V ; I _C =10mA Note 1	75	**	**
	h _{FE2}	3076	V _{CE} =10V ; l _C =150mA Note 1	100	300	-
	h _{FE3}	3076	V _{CE} =10V ; I _C =500mA Note 1	40	*	**
Magnitude of Small-Signal Short- Circuit Forward- Current Transfer Ratio	h _{fe}	3306	V _{CE} =20V, I _C =20mA f=100MHz Note 2	2.5	-	
Output Capacitance	C _{obo}	3236	V _{CB} =10V I _E =0A 100kHz≤ f (1MHz Note 2	-	8	рF
Turn-on Time	t _{on}	-	I _C =150mA I _B =15mA Notes 2, 3	-	35	ns
Turn-off Time	t _{off}	-	I _C =150mA I _B =15mA Notes 2, 4	-	300	ns